



型号: BAS16X

肖特基二极管 SCHOTTKY DIODE

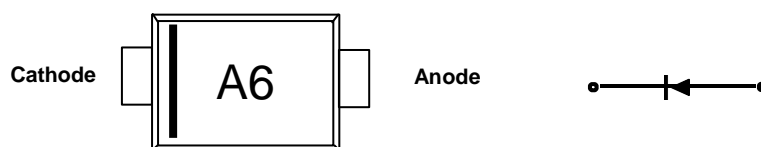
### 主要特性/Features

高速交换应用 High-speed switching applications

### 应用/APPLICATION

高速开关应用 High-speed switching

### 印字/MARKING 等效电路/Equivalent Circuit





**极限参数/Absolute Maximum Ratings(TA=25°C unless otherwise noted)**

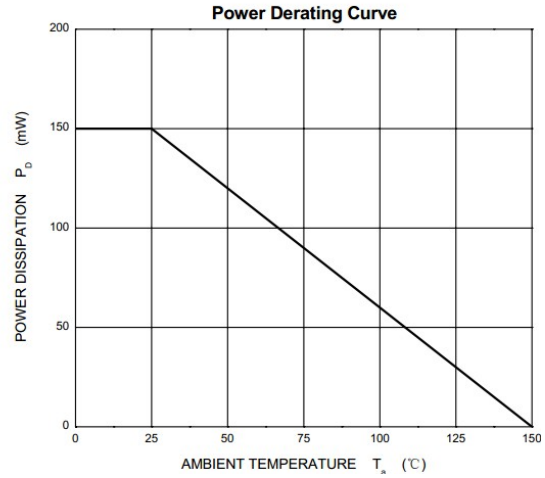
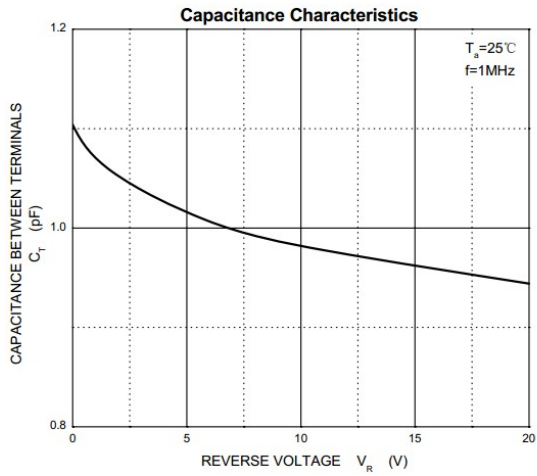
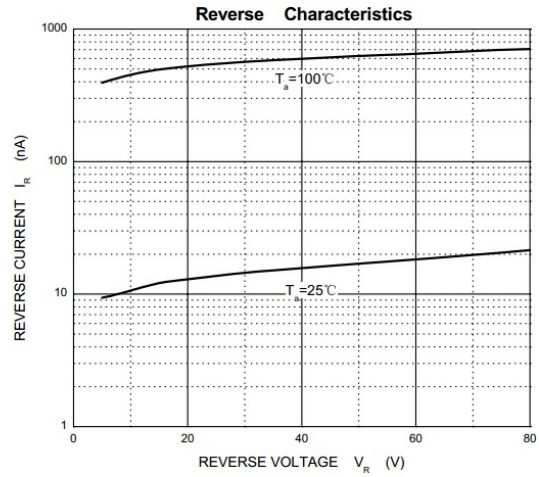
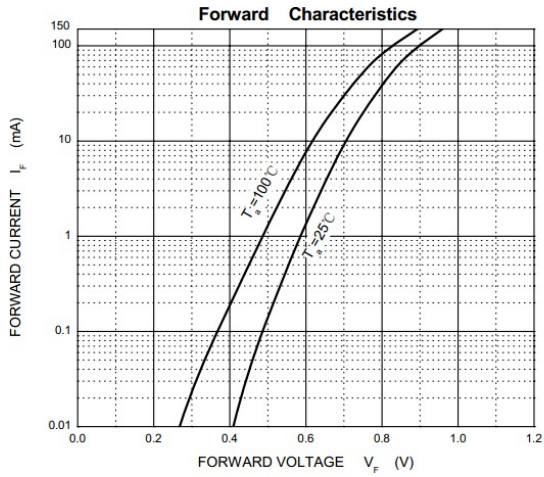
参数/Parameter	符号/ Symbol	数值/Value	单位/Unit
DC Reverse Voltage	VR	75	V
Forward Current	IF	200	mA
Peak Forward Surge Current	IFSM	500	mA
Total Device Dissipation	PD	150	mW
Thermal Resistance Junction to Ambient	Rθ JA	833	°C/mW
Junction and Storage Temperature	Tj, Tstg	150	°C

**电性能参数/Electrical Characteristics (TA=25°C unless otherwise noted )**

Parameter	Symbol	Test condition	Min	Max	Unit
Reverse Breakdown Voltage	V <sub>(BR)</sub>	I <sub>R</sub> =100 μA	75		V
Forward Voltage	V <sub>F1</sub>	I <sub>F</sub> =1mA		715	mV
	V <sub>F2</sub>	I <sub>F</sub> =10mA		855	mV
	V <sub>F3</sub>	I <sub>F</sub> =50mA		1000	mV
	V <sub>F4</sub>	I <sub>F</sub> =150mA		1250	mV
Reverse Current	I <sub>R</sub>	V <sub>R</sub> =75V		1	μ A
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =50mA, R <sub>L</sub> =50Ω		6.0	nS
Diode Capacitance	C <sub>D</sub>	V <sub>R</sub> =0V, f=1MHz		2	pF
Stored Charge	Q <sub>S</sub>	I <sub>F</sub> =10mA, V <sub>R</sub> =5.0V, R <sub>L</sub> =500Ω		45	pC

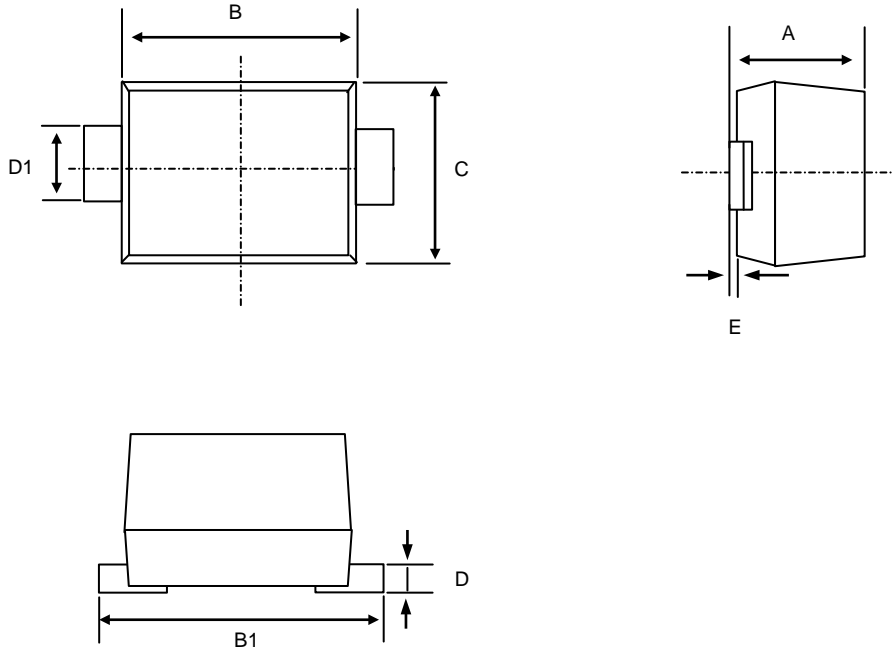


### 典型特性曲线图/Typical Characteristics





成品外观尺寸/SOD-523 Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	0.600	0.650	0.700
B	1.150	1.200	1.250
B1	1.550	1.600	1.650
C	0.750	0.800	0.850
D	0.100	0.110	0.120
D1	0.280	0.300	0.320
E	0.000	-	0.020